



UNI-SEMICONDUCTOR CO., LTD

宇力半导体有限公司

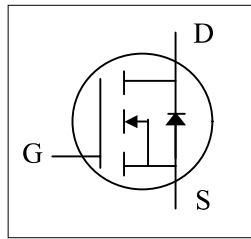


## AP10N10K Data Sheet

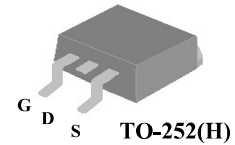
V 1.1

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- ▼ 100% R<sub>g</sub> & UIS Test
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	100V
$R_{DS(ON)}$	115m $\Omega$
$I_D$	10A



## Description

AP10N10K series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance.

## Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Drain Current, $V_{GS}$ @ 10V	10	A
$I_D@T_C=100^\circ C$	Drain Current, $V_{GS}$ @ 10V	6.2	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	28	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	20.8	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	2	W
$E_{AS}$	Single Pulse Avalanche Energy <sup>4</sup>	8	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Value	Units
R <sub>thj-c</sub>	Maximum Thermal Resistance, Junction-case	6	°C/W
R <sub>thj-a</sub>	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>3</sup>	62.5	°C/W

## 1.版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	First Release
2021/11/12	1.1	Layout adjustment

## 2.免责声明

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